风光欣技术资料

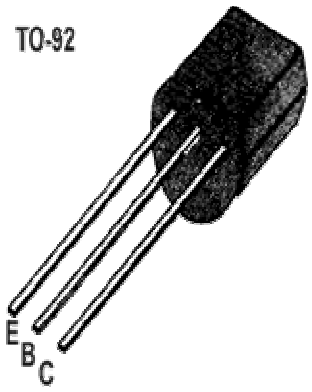
9015

—PNP silicon —

■■**APPLICATION**：General purpose application，Switching application.

■■**MAXIMUM RATINGS**（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-40	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-100	mA
Collector Power Dissipation	P_C	450	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃



■■**ELECTRICAL CHARACTERISTICS**（Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	60		600		V_{CE}= -5 V，Ic= -1 mA
Collector Cut-off Current	I_{CBO}			-0.1	μA	V_{CB}=-50 V，I_E=0
Emitter Cut-off Current	I_{EBO}			-0.1	μA	V_{EB}= -5 V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	-50			V	Ic=-0.1 mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-40			V	Ic=-1 mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	I_E= -0.1mA，Ic=0
Base-Emitter Voltage	$V_{BE(ON)}$			-0.75	V	V_{CE}=-5 V，Ic= -2mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.3	V	Ic=-100 mA，I_B=-10 mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.0	V	Ic=-100 mA，I_B=-10 mA
Gain bandwidth product	f_T	100	190		MHz	Ic= -10 mA，V_{CE}=-5 V
Common Base Output Capacitance	Cob		4.5	7	PF	V_{CB}= -10V，I_E=0，f = 1 MHz
Noise Figure	N_F			10	dB	V_{CE}= -5 V,Ic=-0.2 mA,f=1KHz, Rg= 1KΩ

■■h_{FE} **Classification**

Classification	A	B	C
h_{FE}	60～150	100～300	200～600